



FGA50N100BNTD 1000V, 50A NPT-Trench IGBT CO-PAK

FGA50N100BNTD 1000V, 50A NPT-Trench IGBT CO-PAK

General Description

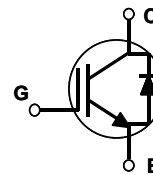
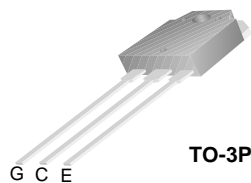
Trench insulated gate bipolar transistors (IGBTs) with NPT technology show outstanding performance in conduction and switching characteristics as well as enhanced avalanche ruggedness. These devices are well suited for Induction Heating (I-H) applications

Features

- High Speed Switching
- Low Saturation Voltage : $V_{CE(sat)} = 2.5 \text{ V @ } I_C = 60\text{A}$
- High Input Impedance
- Built-in Fast Recovery Diode

Application

Micro- Wave Oven, I-H Cooker, I-H Jar, Induction Heater, Home Appliance



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Description	FGA50N100BNTD	Units
V_{CES}	Collector-Emitter Voltage	1000	V
V_{GES}	Gate-Emitter Voltage	± 25	V
I_C	Collector Current @ $T_C = 25^\circ\text{C}$	50	A
	Collector Current @ $T_C = 100^\circ\text{C}$	35	A
$I_{CM(1)}$	Pulsed Collector Current	200	A
I_F	Diode Continuous Forward Current @ $T_C = 100^\circ\text{C}$	15	A
P_D	Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$	156	W
	Maximum Power Dissipation @ $T_C = 100^\circ\text{C}$	63	W
T_J	Operating Junction Temperature	-55 to +150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

Notes :

(1) Repetitive rating : Pulse width limited by max. junction temperature

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}(\text{IGBT})$	Thermal Resistance, Junction-to-Case	--	0.8	$^\circ\text{C/W}$
$R_{\theta JC}(\text{DIODE})$	Thermal Resistance, Junction-to-Case	--	2.4	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	25	$^\circ\text{C/W}$

Package Marking and Ordering Information

Device Marking	Device	Package	Packaging Type	Qty per Tube	Max Qty per Box
FGA50N100BNTD	FGA50N100BNTDTU	TO-3PN	Rail / Tube	30ea	-

Electrical Characteristics of IGBT T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
--------	-----------	-----------------	------	------	------	-------

Off Characteristics

V_{CES}	Collector Emitter Breakdown Voltage	$V_{GE} = 0V, I_C = 1mA$	1000	--	--	V
I_{CES}	Collector Cut-Off Current	$V_{CE} = 1000V, V_{GE} = 0V$	--	--	1.0	mA
I_{GES}	G-E Leakage Current	$V_{GE} = \pm 25, V_{CE} = 0V$	--	--	± 500	nA

On Characteristics

$V_{GE(th)}$	G-E Threshold Voltage	$I_C = 60mA, V_{CE} = V_{GE}$	4.0	5.0	7.0	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C = 10A, V_{GE} = 15V$	--	1.5	1.8	V
		$I_C = 60A, V_{GE} = 15V$	--	2.5	2.9	V

Dynamic Characteristics

C_{ies}	Input Capacitance	$V_{CE}=10V, V_{GE} = 0V, f = 1MHz$	--	6000	--	pF
C_{oes}	Output Capacitance		--	260	--	pF
C_{res}	Reverse Transfer Capacitance		--	200	--	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 600V, I_C = 60A, R_G = 51\Omega, V_{GE}=15V, \text{Resistive Load}, T_C = 25^\circ C$	--	140	--	ns
t_r	Rise Time		--	320	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	630	--	ns
t_f	Fall Time		--	130	250	ns
Q_g	Total Gate Charge	$V_{CE} = 600V, I_C = 60A, V_{GE} = 15V, T_C = 25^\circ C$	--	275	350	nC
Q_{ge}	Gate-Emitter Charge		--	45	--	nC
Q_{gc}	Gate-Collector Charge		--	95	--	nC

Electrical Characteristics of DIODE T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
--------	-----------	-----------------	------	------	------	-------

V_{FM}	Diode Forward Voltage	$I_F = 15A$	--	1.2	1.7	V
		$I_F = 60A$	--	1.8	2.1	V
t_{rr}	Diode Reverse Recovery Time	$I_F = 60A, di/dt = 20 A/us$	--	1.2	1.5	us
I_R	Instantaneous Reverse Current	$V_{RRM} = 1000V$	--	0.05	2	uA

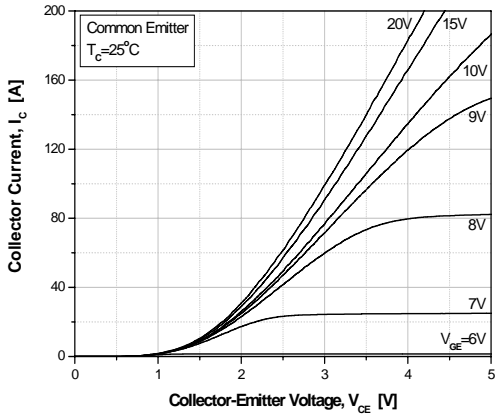


Fig 1. Typical Output Characteristics

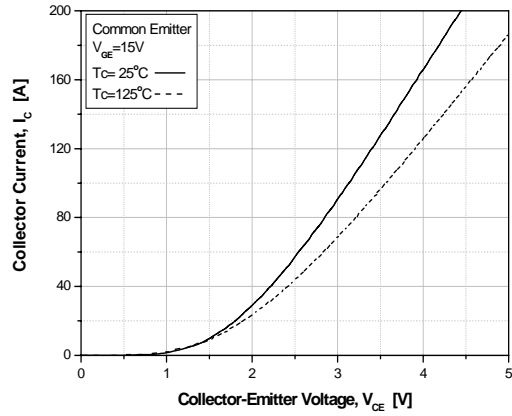


Fig 2. Typical Saturation Voltage Characteristics

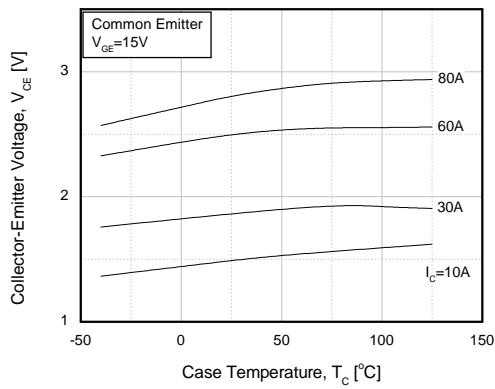


Fig 3. Saturation Voltage vs. Case Temperature at Variant Current Level

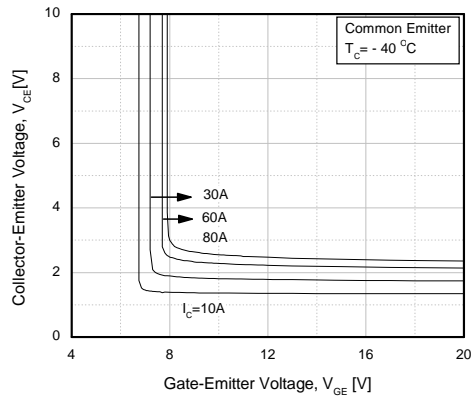


Fig 4. Saturation Voltage vs. V_{GE}

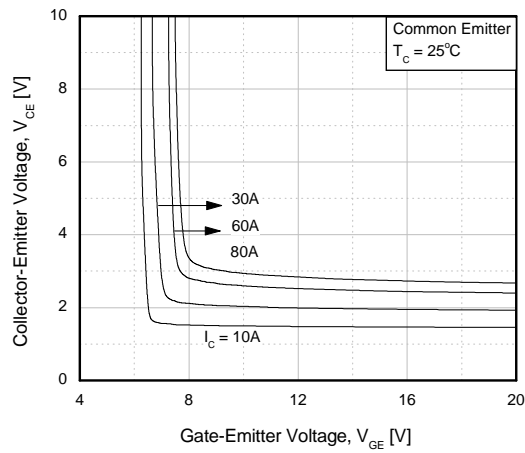


Fig 5. Saturation Voltage vs. V_{GE}

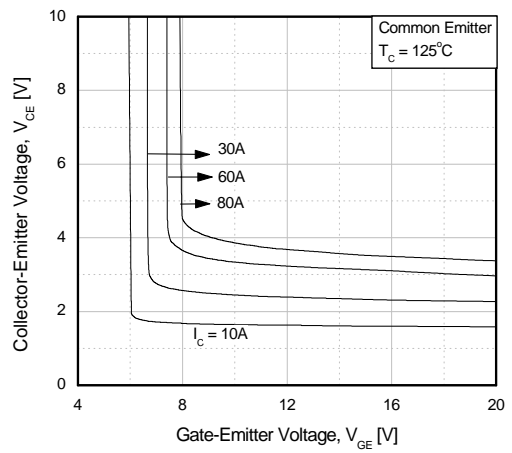


Fig 6. Saturation Voltage vs. V_{GE}

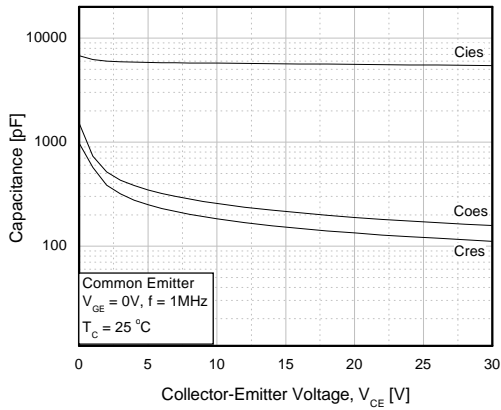


Fig 7. Capacitance Characteristics

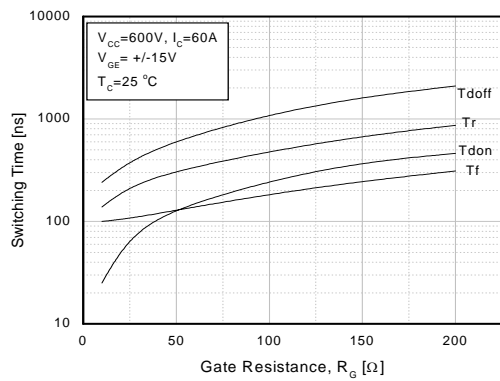


Fig 8. Switching Characteristics vs. Gate Resistance

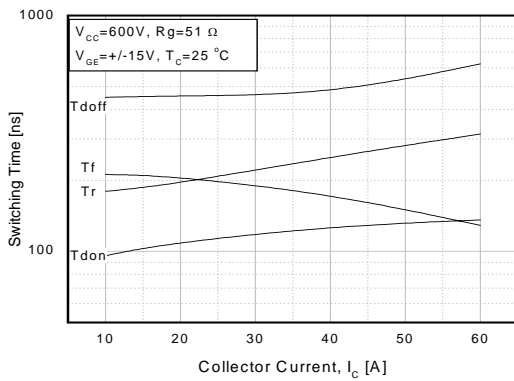


Fig 9. Switching Characteristics vs. Collector Current

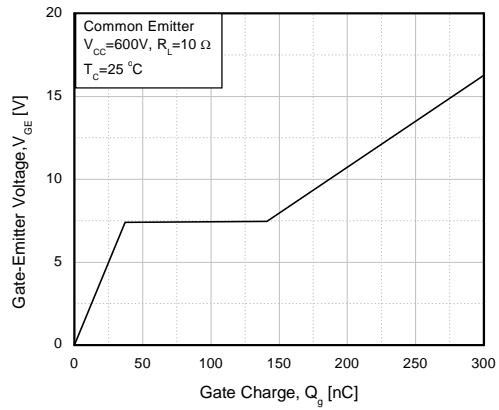


Fig 10. Gate Charge Characteristics

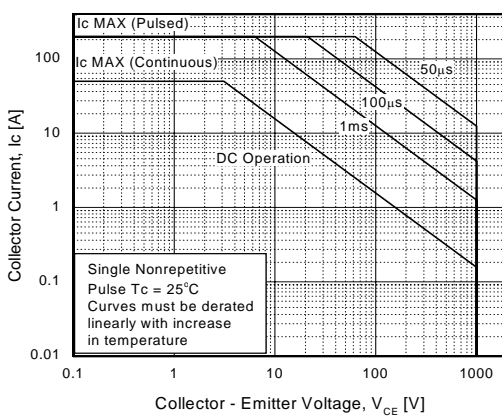


Fig 11. SOA Characteristics

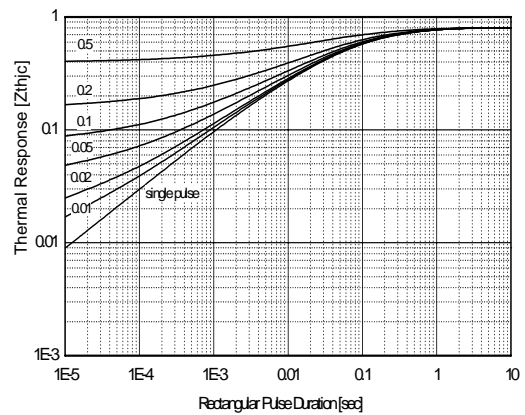


Fig 12. Transient Thermal Impedance of IGBT

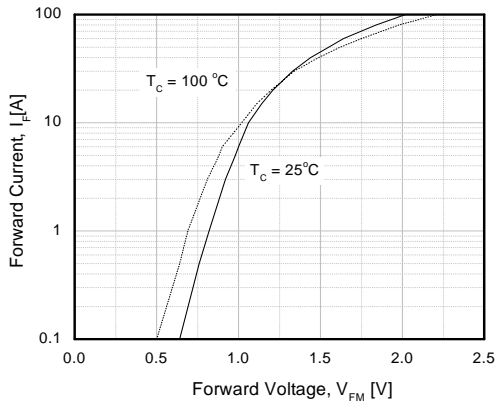


Fig 13. Forward Characteristics

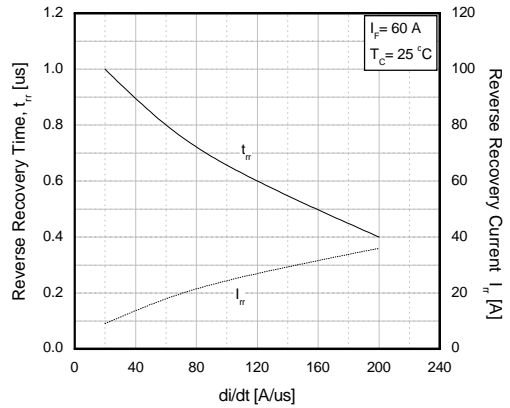


Fig 14. Reverse Recovery Characteristics vs. di/dt

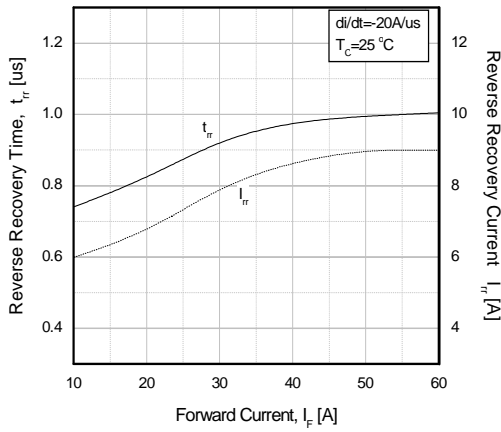


Fig 15. Reverse Recovery Characteristics vs. Forward Current

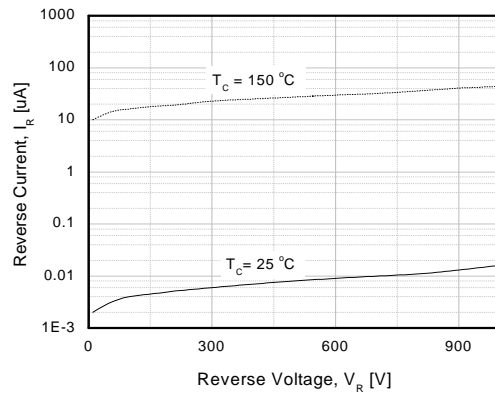


Fig 16. Reverse Current vs. Reverse Voltage

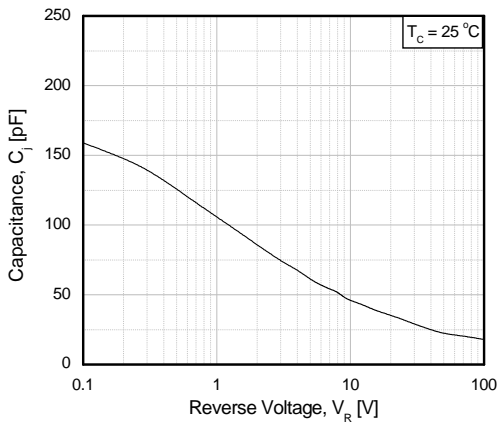
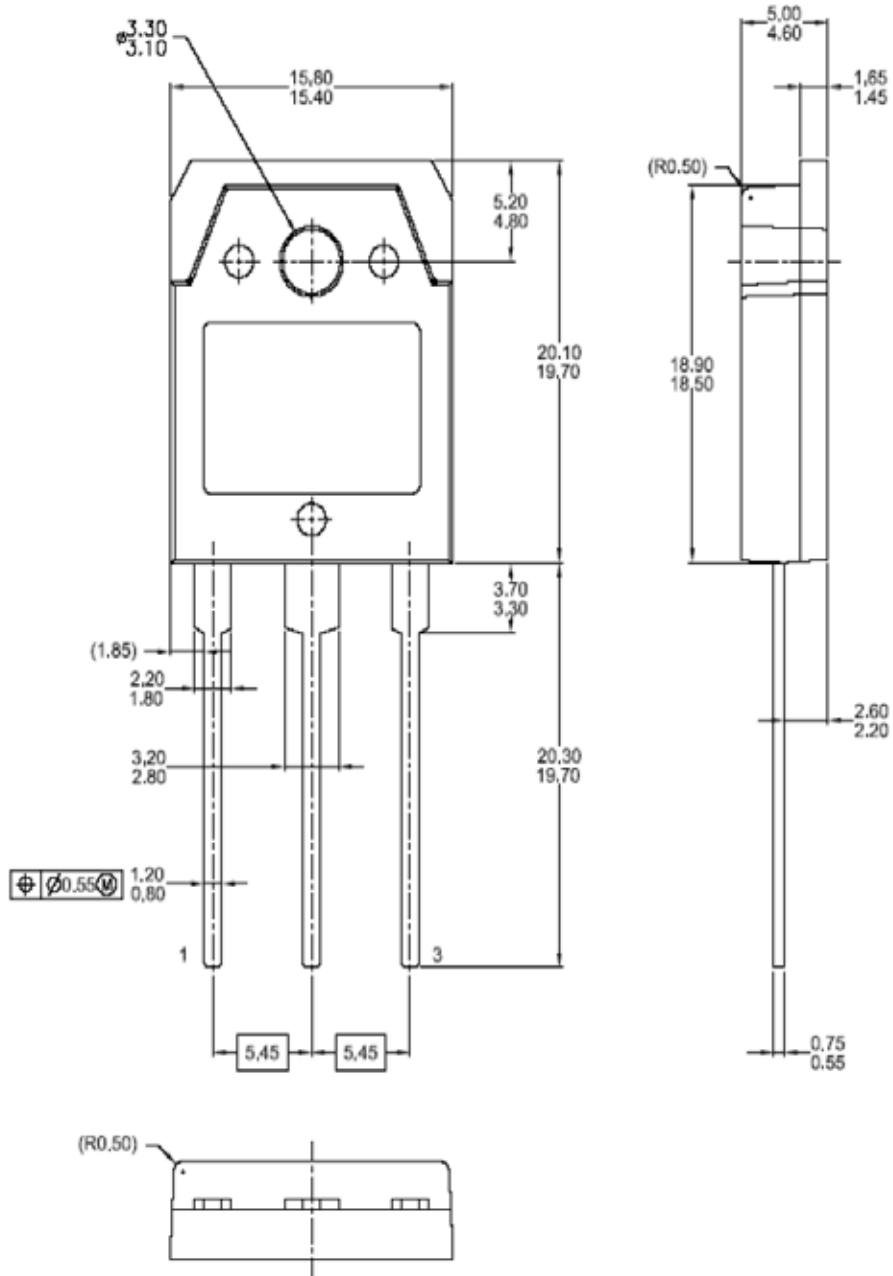


Fig 17. Junction capacitance

Mechanical Dimensions

TO-3PN







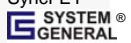


Dimensions in Millimeters



TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

- | | | | |
|---|---|---|---|
| Build it Now™ | FRFET® | Programmable Active Droop™ | 
TinyBoost™
TinyBuck™
TinyLogic®
TINYOPTO™
TinyPower™
TinyPWM™
TinyWire™
μSerDes™

UHC®
Ultra FRFET™
UniFET™
VCX™
VisualMax™
XS™ |
| CorePLUS™ | Global Power Resource SM | QFET® | |
| CorePOWER™ | Green FPS™ | QS™ | |
| CROSSVOLT™ | Green FPS™ e-Series™ | Quiet Series™ | |
| CTL™ | GTO™ | RapidConfigure™ | |
| Current Transfer Logic™ | IntelliMAX™ |  ™ | |
| EcoSPARK® | ISOPLANAR™ | Saving our world, 1mW/W/kW at a time™ | |
| EfficientMax™ | MegaBuck™ | SmartMax™ | |
| EZSWITCH™ * | MICROCOUPLER™ | SMART START™ | |
|  ™ | MicroFET™ | SPM® | |
|  ® | MicroPak™ | STEALTH™ | |
| Fairchild® | MillerDrive™ | SuperFET™ | |
| Fairchild Semiconductor® | MotionMax™ | SuperSOT™-3 | |
| FACT Quiet Series™ | Motion-SPM™ | SuperSOT™-6 | |
| FACT® | OPTOLOGIC® | SuperSOT™-8 | |
| FAST® | OPTOPLANAR® | SupreMOS™ | |
| FastvCore™ |  ® | SyncFET™ | |
| FlashWriter® * | PDP SPM™ |  ® | |
| FPS™ | Power-SPM™ | The Power Franchise® | |
| F-PFS™ | PowerTrench® | | |
| | PowerXS™ | | |

* EZSWITCH™ and FlashWriter® are trademarks of System General Corporation, used under license by Fairchild Semiconductor.

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufacturers of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed applications, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handling and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address any warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.



Стандарт Электрон Связь

Мы молодая и активно развивающаяся компания в области поставок электронных компонентов. Мы поставляем электронные компоненты отечественного и импортного производства напрямую от производителей и с крупнейших складов мира.

Благодаря сотрудничеству с мировыми поставщиками мы осуществляем комплексные и плановые поставки широчайшего спектра электронных компонентов.

Собственная эффективная логистика и склад в обеспечивает надежную поставку продукции в точно указанные сроки по всей России.

Мы осуществляем техническую поддержку нашим клиентам и предпродажную проверку качества продукции. На все поставляемые продукты мы предоставляем гарантию .

Осуществляем поставки продукции под контролем ВП МО РФ на предприятия военно-промышленного комплекса России , а также работаем в рамках 275 ФЗ с открытием отдельных счетов в уполномоченном банке. Система менеджмента качества компании соответствует требованиям ГОСТ ISO 9001.

Минимальные сроки поставки, гибкие цены, неограниченный ассортимент и индивидуальный подход к клиентам являются основой для выстраивания долгосрочного и эффективного сотрудничества с предприятиями радиоэлектронной промышленности, предприятиями ВПК и научно-исследовательскими институтами России.

С нами вы становитесь еще успешнее!

Наши контакты:

Телефон: +7 812 627 14 35

Электронная почта: sales@st-electron.ru

Адрес: 198099, Санкт-Петербург,
Промышленная ул, дом № 19, литера Н,
помещение 100-Н Офис 331